

Docket No.: M4065.0278/P278
(PATENT)

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Patent Application of:
Kevin L. Beaman, et al.

Application No.: 09/653,281

Group Art Unit: 2812

Filed: August 31, 2000

Examiner: Richard A. Booth

For: USE OF ATOMIC OXIDATION FOR
FABRICATION OF OXIDE-NITRIDE-
OXIDE STACK FOR FLASH MEMORY
DEVICES

AMENDMENT

Commissioner for Patents
Washington, DC 20231

Dear Sir:

Applicants amend the above-referenced application as follows.

In the Claims:

Please cancel claims 5, 17 and 19.

Please rewrite claims 1, 16, and 31 as follows:

1. (Twice amended) A method of forming a flash memory cell, comprising:

forming a tunnel oxide on a substrate;

forming a first conductor layer over said tunnel oxide;

forming an insulating layer over said first conductor layer, said insulating layer comprising a first oxide layer over said first conductor layer, a nitride layer over said first